NPN Epitaxial Planar Silicon Transistors



2SC4523

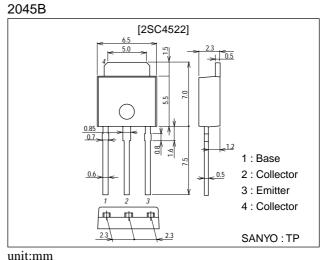
High-Speed Switching Applications

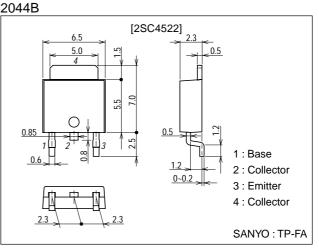
Features

- · Adoption of FBET, MBIT process.
- · Large current capacity.
- · Low collector-to-emitter saturation voltage.
- · Fast switching speed.

Package Dimensions

unit:mm





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Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		60	V
Collector-to-Emitter Voltage	VCEO		45	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	Ι _C		8	A
Collector Current (Pulse)	ICP		12	A
Collector Dissipation	PC		1	W
		Tc=25°C	15	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

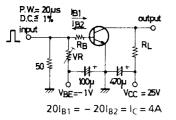
Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =45V, I _E =0			1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =2V, I _C =0			10	μΑ
DC Current Gain	h _{FE} 1	V _{CE} =2V, I _C =500mA	100*		400*	
	h _{FE} 2	V _{CE} =2V, I _C =8A	40			
Gain-Bandwidth Product	fT	V _{CE} =2V, I _C =500mA		250		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		65		pF
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =4A, I _B =200mA		0.25	0.7	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =4A, I _B =200mA		0.95	1.3	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =100μA, I _E =0	60			V
Collector-to-Emitter Breakdown Voltage	V _(BR) CEO	I _C =1mA, R _{BE} =∞	45			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Turn-ON Time	ton	See specified test circuit.		50	100	ns
Storage Time	t _{stg}	See specified test circuit.		150	270	ns
Fall Time	tf	See specified test circuit.		180	350	ns

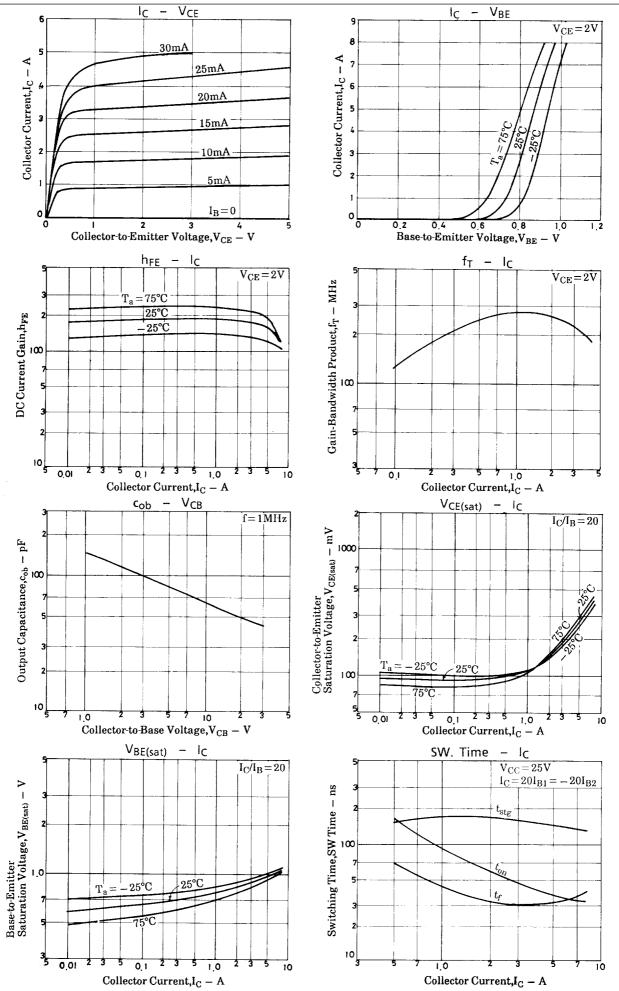
 \ast : The 2SC4523 is classified by 500mA h_{FE} as follows :

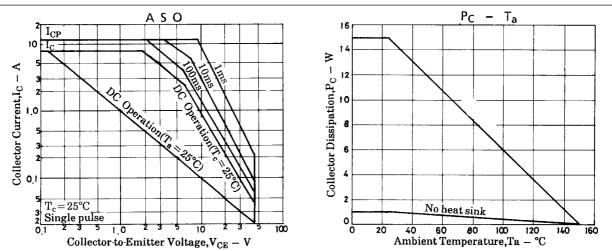
100 R 200 140 S 280 200 T 400

Switching Time Test Circuit



Unit (resistance : Ω , capacitance : F)





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